

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 7)	Steady State	T _A = +25°C T _A = +70°C	I _D	630 500	mA
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	0.5	A
Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)			EZ	200	mJ
Peak Power Dissipation, Drain-to-Source (Non repetitive current square pulse 1.0ms duration) (T _J Initial = +85°C)			PPK	20	W
Load Dump Pulse, Drain-to-Source, R _{SOURCE} = 0.5Ω, t = 300ms) (For Relay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)			ELD1	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: R _{SOURCE} = 10Ω, t = 2.0ms) (For Relay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)			ELD2	100	V
Inductive Switching Transient 2, Drain-to-Source (Waveform: R _{SOURCE} = 4.0Ω, t = 50μs) (For Relay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)			ELD3	300	V
Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80Ω or more)			Rev-Bat	-14	V
Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)			Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

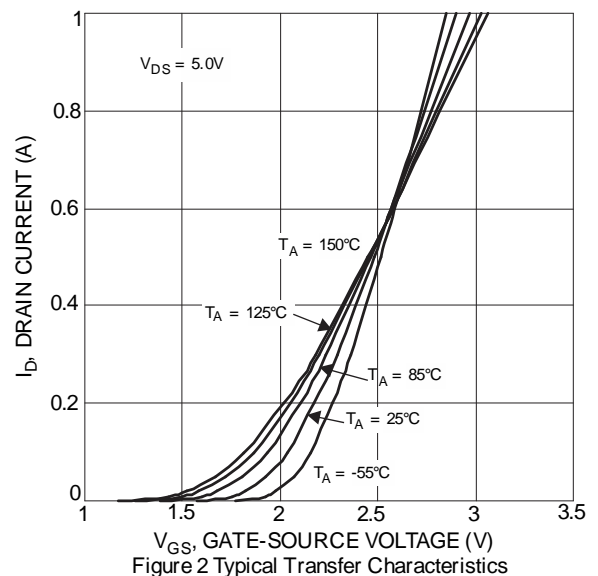
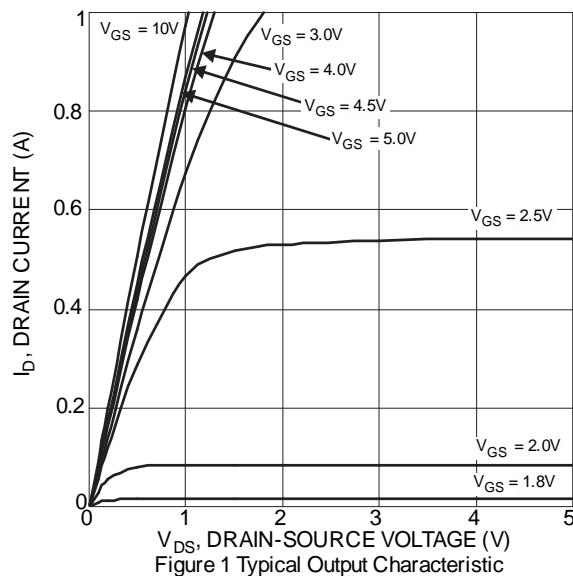
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P _D	820	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	154	°C/W
Total Power Dissipation (Note 7)		P _D	1,090	mW
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{θJA}	116	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	50 0.5	μA	V _{DS} = 60V, V _{GS} = 0V V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±90 ±60	μA	V _{GS} = ±5V, V _{DS} = 0V V _{GS} = ±3V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	—	2.0	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.1 1.4	1.8 2.4	Ω	V _{GS} = 5V, I _D = 0.15A
						V _{GS} = 3V, I _D = 0.15A
Forward Transfer Admittance	Y _{fs}	80	—	—	ms	V _{DS} = 12V, I _D = 0.15A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 0.15A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	12.9	—	pF	V _{DS} = 12V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	17	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	0.84	—	pF	
Total Gate Charge	Q _g	—	0.74	—	nC	V _{GS} = 5V, V _{DS} = 12V, I _D = 150mA
Gate-Source Charge	Q _{gs}	—	0.19	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.16	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	131	—	ns	V _{DD} = 12V, V _{GS} = 5V
Turn-On Rise Time	t _r	—	301	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	582	—	ns	
Turn-Off Fall Time	t _f	—	440	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



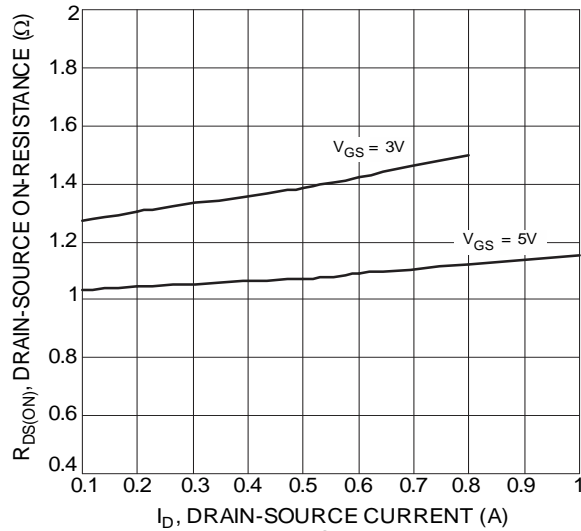


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

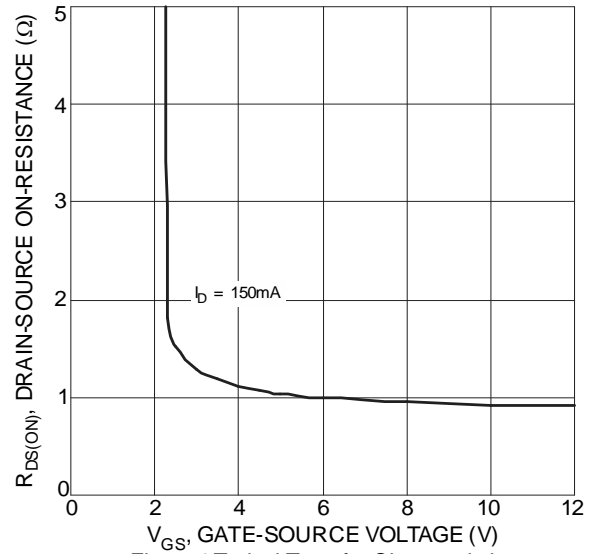


Figure 4 Typical Transfer Characteristic

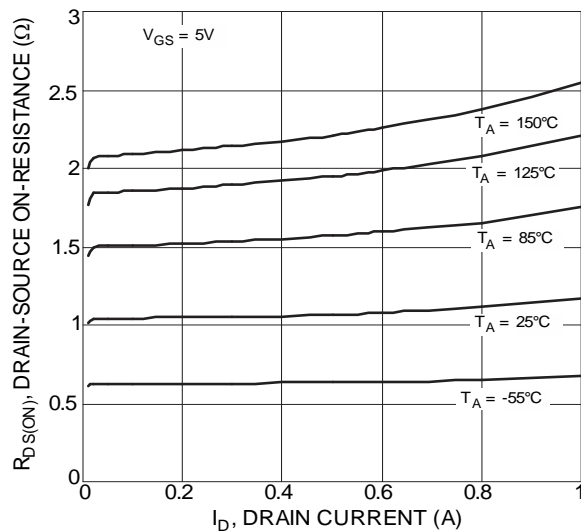


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

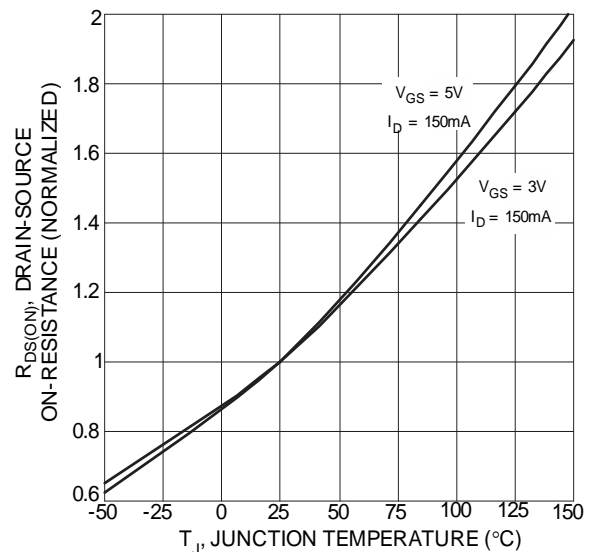


Figure 6 On-Resistance Variation with Temperature

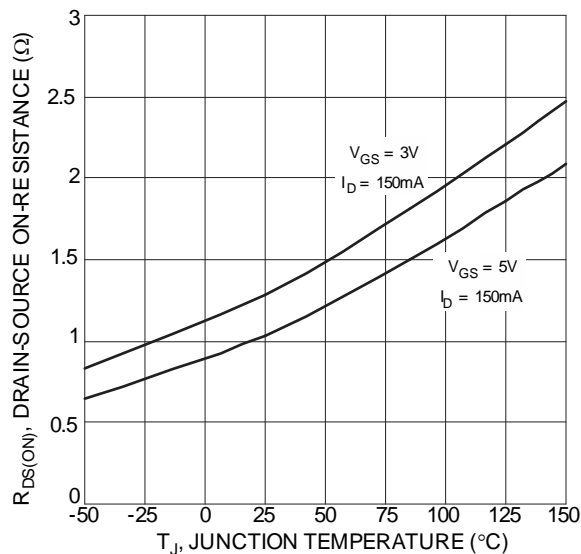


Figure 7 On-Resistance Variation with Temperature

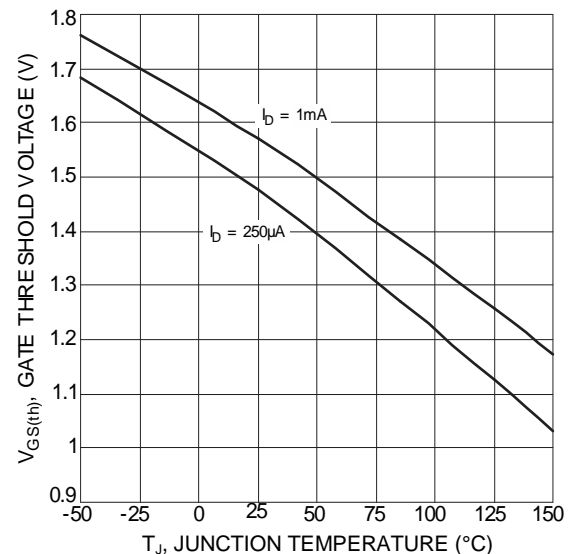
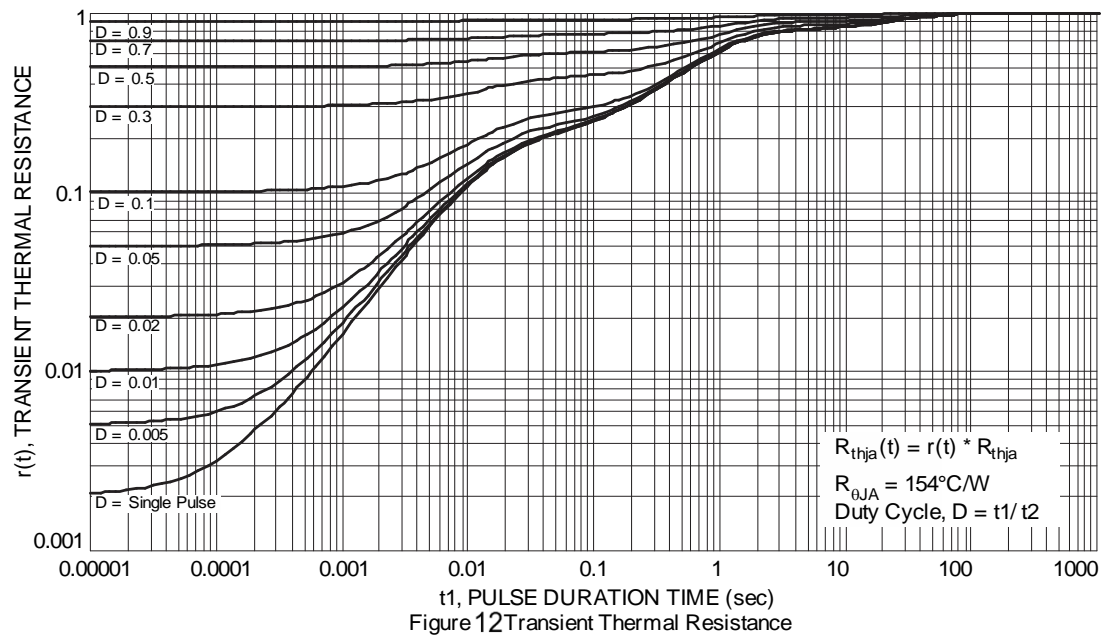
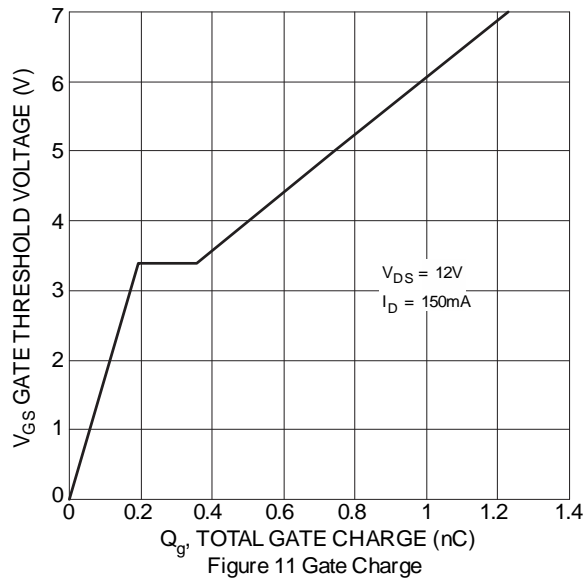
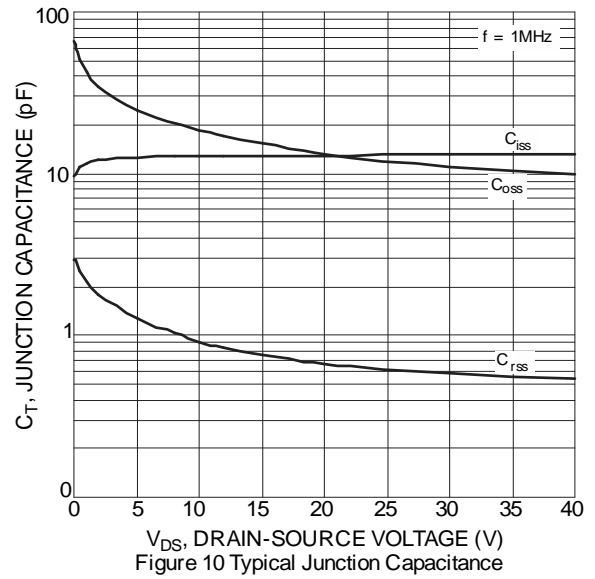
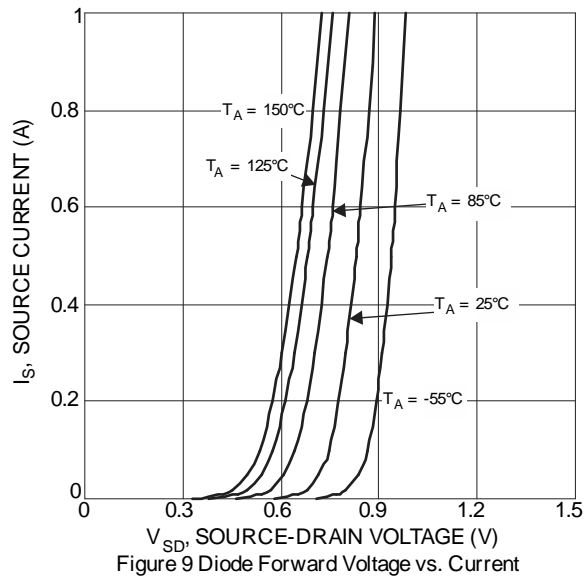


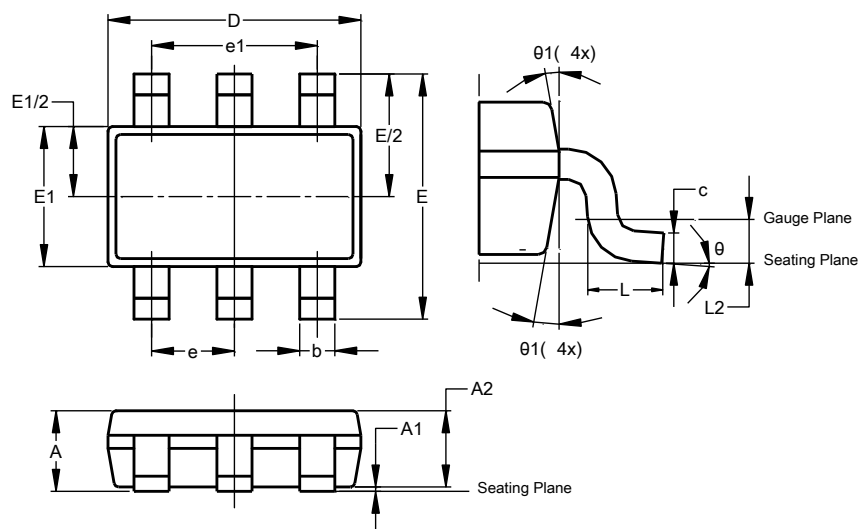
Figure 8 Gate Threshold Variation vs. Junction Temperature



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

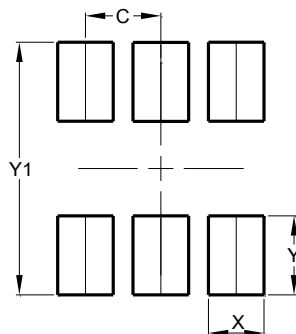


TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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